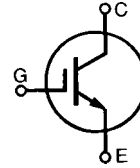


High Speed IGBT

IXSH/IXST 30N60B
IXSH/IXST 30N60C

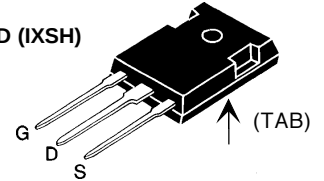
Short Circuit SOA Capability



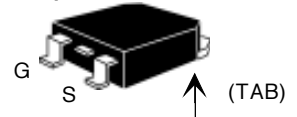
V_{CES}	I_{CES}	t_{fi}
600 V	2.0 V	140 ns
600 V	2.5 V	70 ns

Symbol	Test Conditions	Maximum Ratings	
V_{CES}	$T_J = 25^\circ\text{C}$ to 150°C	600	V
V_{CGR}	$T_J = 25^\circ\text{C}$ to 150°C ; $R_{GE} = 1\text{ M}\Omega$	600	V
V_{GES}	Continuous	± 20	V
V_{GEM}	Transient	± 30	V
I_{C25}	$T_C = 25^\circ\text{C}$	55	A
I_{C90}	$T_C = 90^\circ\text{C}$	30	A
I_{CM}	$T_C = 25^\circ\text{C}$, 1 ms	110	A
SSOA (RBSOA)	$V_{GE} = 15\text{ V}$, $T_J = 125^\circ\text{C}$, $R_G = 2.7\ \Omega$ Clamped inductive load, $V_{CC} = 0.8 V_{CES}$	$I_{CM} = 60$ @ $0.8 V_{CES}$	A
t_{SC} (SCSOA)	$V_{GE} = 15\text{ V}$, $V_{CE} = 360\text{ V}$, $T_J = 125^\circ\text{C}$ $R_G = 33\ \Omega$, non repetitive	10	μs
P_C	$T_C = 25^\circ\text{C}$	200	W
T_J		-55 ... +150	$^\circ\text{C}$
T_{JM}		150	$^\circ\text{C}$
T_{stg}		-55 ... +150	$^\circ\text{C}$
M_d	Mounting torque	(TO-247)	1.13/10 Nm/lb.in.
Weight		TO-247	6 g
		TO-268	4 g
Maximum lead temperature for soldering 1.6 mm (0.062 in.) from case for 10 s		300	$^\circ\text{C}$

TO-247 AD (IXSH)



TO-268 (D3) (IXST)



G = Gate
S = Source

TAB = Drain

Features

- International standard packages
- Short Circuit SOA capability
- High frequency IGBT
- New generation HDMOS™ process

Applications

- AC motor speed control
- DC servo and robot drives
- DC choppers
- Uninterruptible power supplies (UPS)
- Switch-mode and resonant-mode power supplies

Advantages

- Easy to mount with 1 screw (isolated mounting screw hole)
- Surface mountable, high power case style
- Reduce assembly time and cost
- High power density

Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
BV_{CES}	$I_C = 250\ \mu\text{A}$, $V_{GE} = 0\text{ V}$	600		V
$V_{GE(th)}$	$I_C = 2.5\text{ mA}$, $V_{CE} = V_{GE}$	4		V
I_{CES}	$V_{CE} = 0.8 V_{CES}$, $V_{GE} = 0\text{ V}$ $T_J = 25^\circ\text{C}$ $T_J = 125^\circ\text{C}$			100 μA 1 mA
I_{GES}	$V_{CE} = 0\text{ V}$, $V_{GE} = \pm 20\text{ V}$			$\pm 100\text{ nA}$
$V_{CE(sat)}$	$V_{GE} = 15\text{ V}$; $I_C = I_{C90}$	30N60B 30N60C		2.0 V 2.5 V

Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
g_{fs}	$I_C = I_{C90}$; $V_{CE} = 10\text{ V}$, Pulse test, $t \leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$	10		S
C_{ies}	$V_{CE} = 25\text{ V}$, $V_{GE} = 0\text{ V}$, $f = 1\text{ MHz}$		3100	pF
C_{oes}			240	pF
C_{res}			30	pF
Q_g	$I_C = I_{C90}$, $V_{GE} = 15\text{ V}$, $V_{CE} = 0.5 V_{CES}$		100	nC
Q_{ge}			30	nC
Q_{gc}			38	nC
$t_{d(on)}$	Inductive load, $T_J = 25^\circ\text{C}$		30	ns
t_{ri}			30	ns
$t_{d(off)}$		$I_C = I_{C90}$, $V_{GE} = 15\text{ V}$	30N60B 150	270 ns
		$V_{CE} = 0.8 V_{CES}$, $R_G = 4.7\text{ }\Omega$	30N60C 90	150 ns
		Note 1	30N60B 140	270 ns
t_{fi}			30N60C 70	120 ns
E_{off}			30N60B 1.5	2.5 mJ
			30N60C 0.7	1.2 mJ
$t_{d(on)}$	Inductive load, $T_J = 125^\circ\text{C}$		35	ns
t_{ri}			35	ns
E_{on}		$I_C = I_{C90}$, $V_{GE} = 15\text{ V}$	0.5	mJ
		$V_{CE} = 0.8 V_{CES}$, $R_G = 4.7\text{ }\Omega$		
		Note 1	30N60B 270	ns
$t_{d(off)}$			30N60C 150	ns
t_{fi}			30N60B 250	ns
			30N60C 140	ns
E_{off}			30N60B 2.5	mJ
			30N60C 1.2	mJ
R_{thJC}				0.62 K/W
R_{thCK}	(TO-247)		0.25	K/W

Notes: 1. Switching times may increase for V_{CE} (Clamp) $> 0.8 V_{CES}$, higher T_J or increased R_G .

Min Recommended Footprint

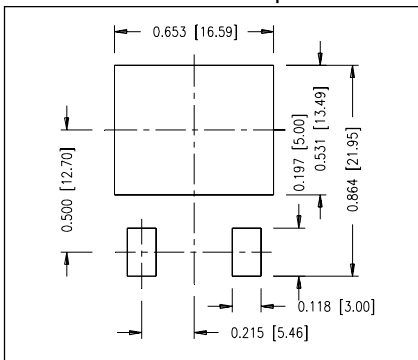


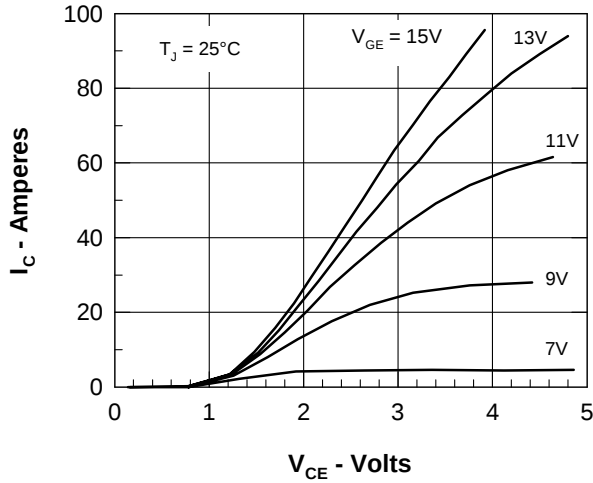
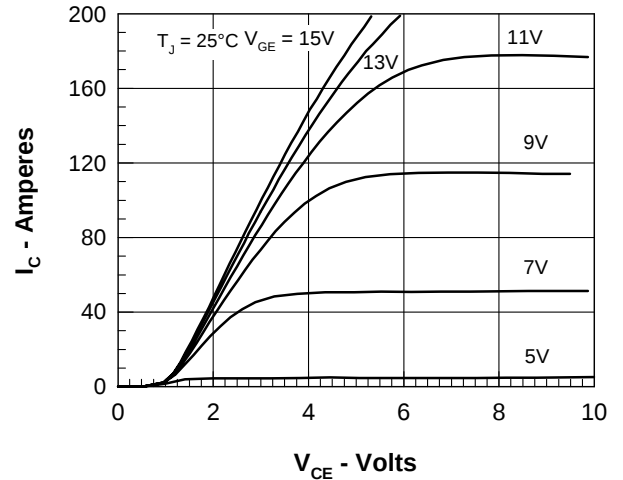
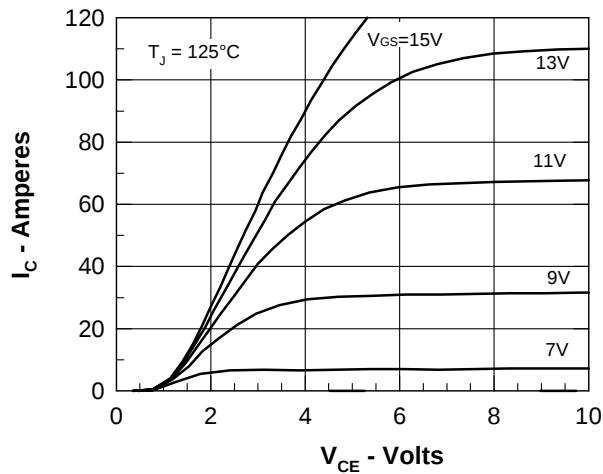
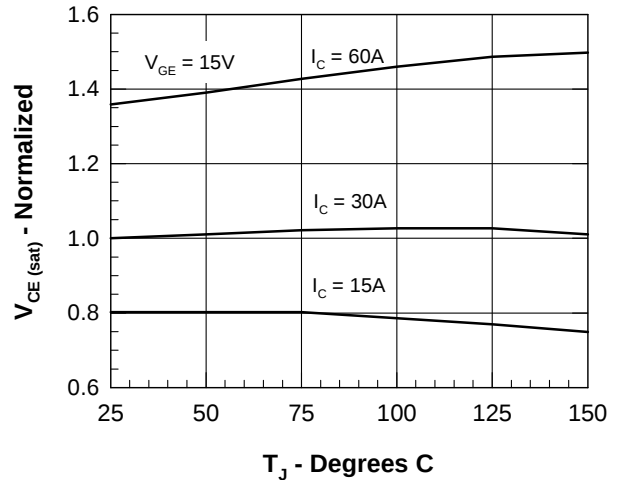
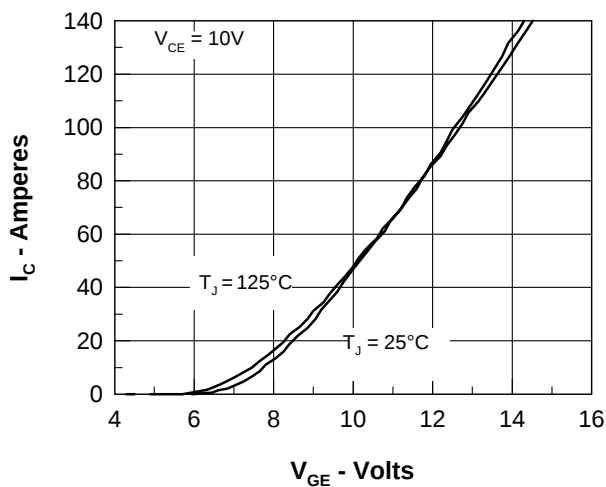
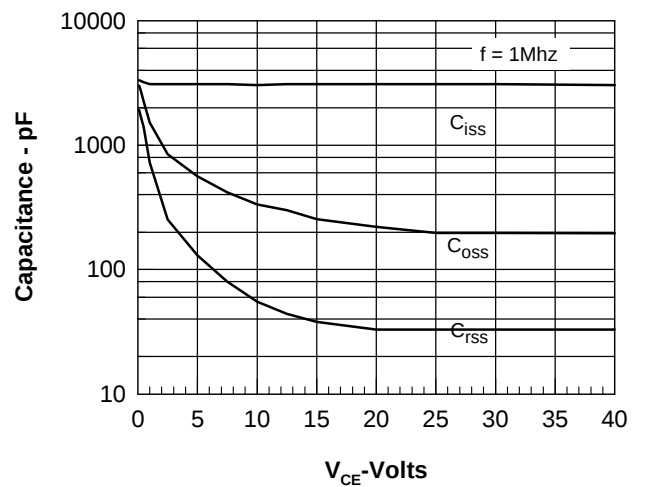
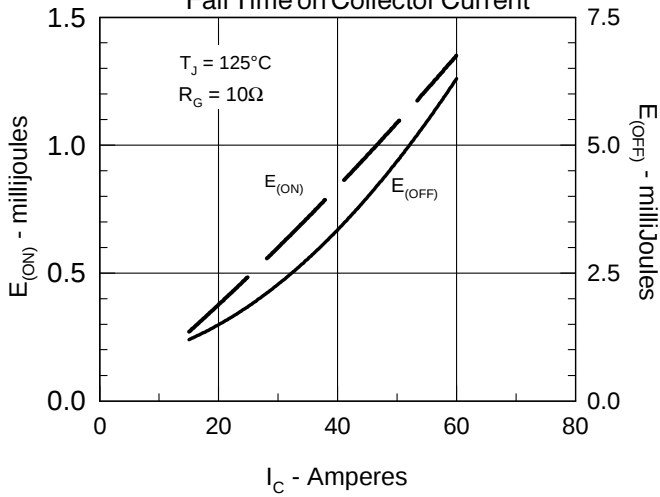
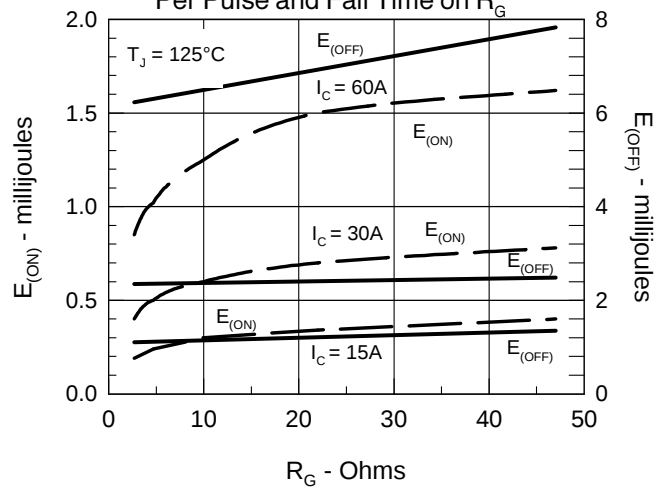
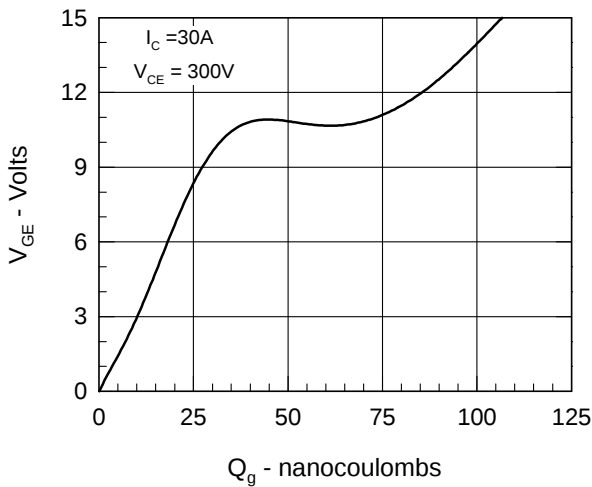
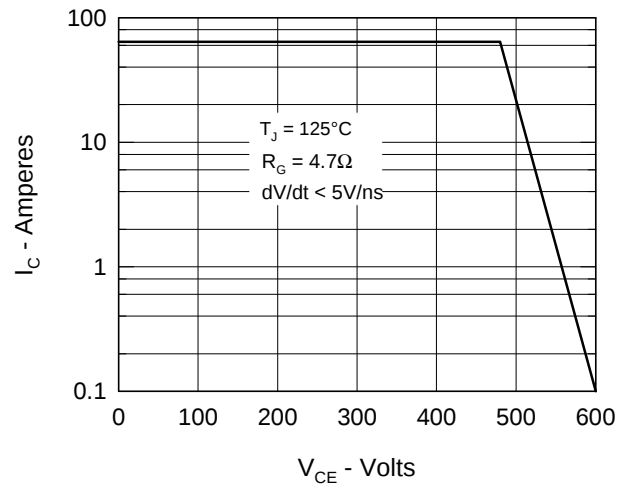
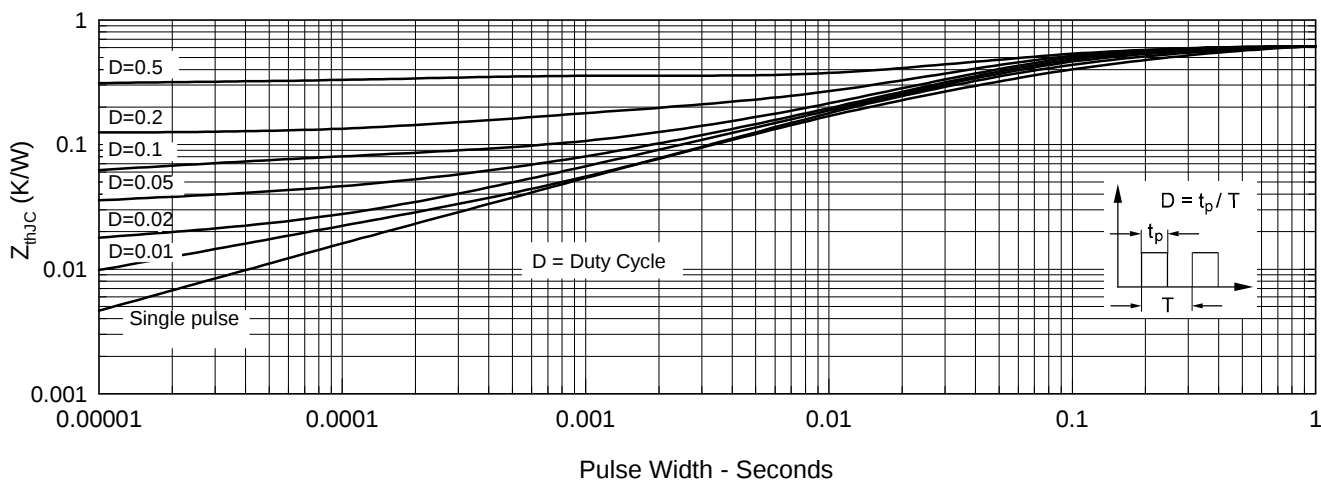
Fig.1 Saturation Characteristics

Fig.2 Output Characteristics

Fig.3 Collector-Emitter Voltage vs. Gate-Emitter Voltage

Fig.4 Temperature Dependence of Output Saturation Voltage

Fig.5 Input Admittance

Fig.6 Temperature Dependence of Breakdown and Threshold Voltage


Fig.7 Turn-Off Energy per Pulse and Fall Time on Collector Current

Fig.8 Dependence of Turn-Off Energy Per Pulse and Fall Time on R_G

Fig.9 Gate Charge Characteristic Curve

Fig.10 Turn-Off Safe Operating Area

Fig.11 Transient Thermal Impedance


IXYS reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:

4,835,592	4,881,106	5,017,508	5,049,961	5,187,117	5,486,715
4,850,072	4,931,844	5,034,796	5,063,307	5,237,481	5,381,025